

## N-Channel 60 V (D-S) MOSFET

### PRODUCT SUMMARY

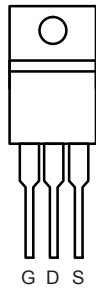
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>a</sup>
60	0.024 at $V_{GS} = 10$ V	50
	0.028 at $V_{GS} = 4.5$ V	40

### FEATURES

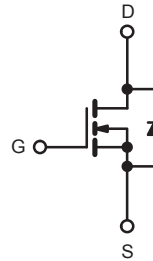
- Halogen-free According to IEC 61249-2-21 Definition
- Surface Mount
- Available in Tape and Reel
- Dynamic dV/dt Rating
- Logic-Level Gate Drive
- Fast Switching
- Compliant to RoHS Directive 2002/95/EC


**RoHS\***  
 COMPLIANT

TO-220AB



Top View



N-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

PARAMETER				SYMBOL	LIMIT	UNIT
Drain-Source Voltage				$V_{DS}$	60	V
Gate-Source Voltage				$V_{GS}$	$\pm 20$	
Continuous Drain Current <sup>f</sup>	$V_{GS}$ at 10 V	$T_C = 25\text{ }^{\circ}\text{C}$	$I_D$	50	A	
Continuous Drain Current		$T_C = 100\text{ }^{\circ}\text{C}$		36		
Pulsed Drain Current <sup>a</sup>			$I_{DM}$	200		
Linear Derating Factor				1.0	W/ $^{\circ}\text{C}$	
Linear Derating Factor (PCB Mount) <sup>e</sup>				0.025		
Single Pulse Avalanche Energy <sup>b</sup>			$E_{AS}$	400	mJ	
Maximum Power Dissipation	$T_C = 25\text{ }^{\circ}\text{C}$		$P_D$	150	W	
Maximum Power Dissipation (PCB Mount) <sup>e</sup>	$T_A = 25\text{ }^{\circ}\text{C}$			3.7		
Peak Diode Recovery $dV/dt$ <sup>c</sup>			$dV/dt$	4.5	V/ns	
Operating Junction and Storage Temperature Range			$T_J, T_{stg}$	- 55 to + 175	$^{\circ}\text{C}$	
Soldering Recommendations (Peak Temperature) <sup>d</sup>	for 10 s			300 <sup>d</sup>		

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 25$  V, starting  $T_J = 25$  °C,  $L = 179$   $\mu$ H,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 51$  A (see fig. 12).
- $I_{SD} \leq 51$  A,  $di/dt \leq 250$  A/ $\mu$ s,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 175$  °C.
- 1.6 mm from case.
- When mounted on 1" square PCB (FR-4 or G-10 material).
- Current limited by the package, (die current = 51 A).

**THERMAL RESISTANCE RATINGS**

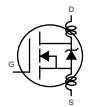

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Maximum Junction-to-Ambient (PCB Mount) <sup>a</sup>	$R_{thJA}$	-	40	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	1.0	

**Note**

a. When mounted on 1" square PCB (FR-4 or G-10 material).

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**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0, I_D = 250\text{ }\mu\text{A}$		60	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, $I_D = 1\text{ mA}$		-	0.070	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		1.0	-	2.5	
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 10\text{ V}$		-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$		-	-	25	$\mu\text{A}$
		$V_{DS} = 48\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^{\circ}\text{C}$		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 21\text{ A}^b$	-	0.024	-	$\Omega$
		$V_{GS} = 4.5\text{ V}$	$I_D = 15\text{ A}^b$	-	0.028	-	
Forward Transconductance	$g_{fs}$	$V_{DS} = 25\text{ V}, I_D = 21\text{ A}^b$		23	-	-	S
Dynamic							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V},$ $V_{DS} = 25\text{ V},$ $f = 1.0\text{ MHz, see fig. 5}$		-	190		pF
Output Capacitance	$C_{oss}$			-	920	-	
Reverse Transfer Capacitance	$C_{rss}$			-	170	-	
Total Gate Charge	$Q_g$	$V_{GS} = 5.0\text{ V}$	$I_D = 51\text{ A}, V_{DS} = 48\text{ V},$ see fig. 6 and 13 <sup>b</sup>	-	-	66	nC
Gate-Source Charge	$Q_{gs}$			-	-	12	
Gate-Drain Charge	$Q_{gd}$			-	-	43	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30\text{ V}, I_D = 51\text{ A},$ $R_g = 4.6\text{ }\Omega, R_D = 0.56\text{ }\Omega, \text{ see fig. 10}^b$		-	17	-	ns
Rise Time	$t_r$			-	230	-	
Turn-Off Delay Time	$t_{d(off)}$			-	2	-	
Fall Time	$t_f$			-	110	-	
Internal Drain Inductance	$L_D$	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	nH
Internal Source Inductance	$L_S$			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	50 <sup>c</sup>	A
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$			-	-	200	
Body Diode Voltage	$V_{SD}$	$T_J = 25\text{ }^{\circ}\text{C}, I_S = 51\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	2.5	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^{\circ}\text{C}, I_F = 51\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$		-	130	180	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			-	0.84	1.3	$\mu\text{C}$
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )					

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).  
 b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .  
 c. Current limited by the package, (Die Current = 51 A).

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics,  $T_C = 25^\circ\text{C}$** 

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 2 - Typical Output Characteristics,  $T_C = 150^\circ\text{C}$** 

**Fig. 4 - Normalized On-Resistance vs. Temperature**



Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



Fig. 7 - Typical Source-Drain Diode Forward Voltage



Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

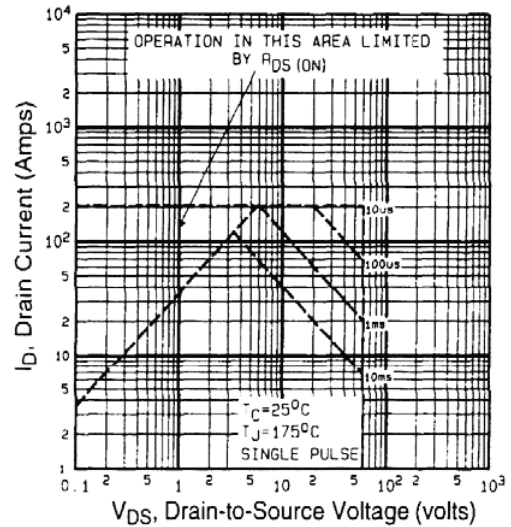


Fig. 8 - Maximum Safe Operating Area



Fig. 9 - Maximum Drain Current vs. Case Temperature

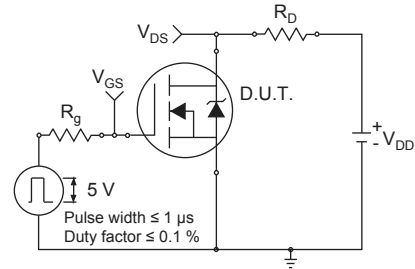


Fig. 10a - Switching Time Test Circuit

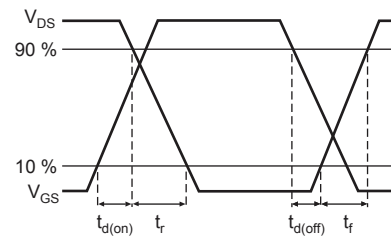


Fig. 10b - Switching Time Waveforms



Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

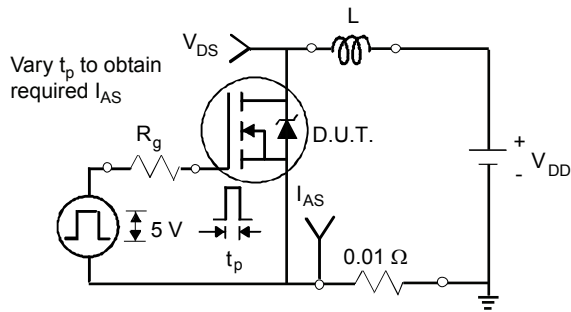


Fig. 12a - Unclamped Inductive Test Circuit

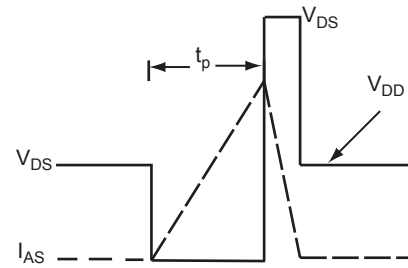


Fig. 12b - Unclamped Inductive Waveforms



Fig. 12c - Maximum Avalanche Energy vs. Drain Current



Fig. 13a - Basic Gate Charge Waveform

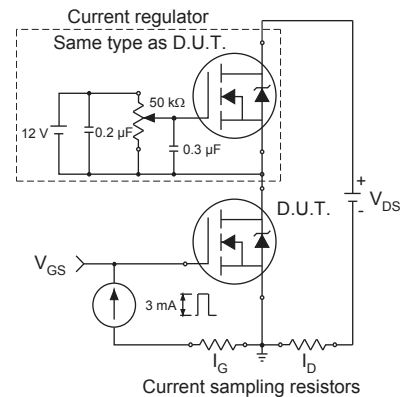
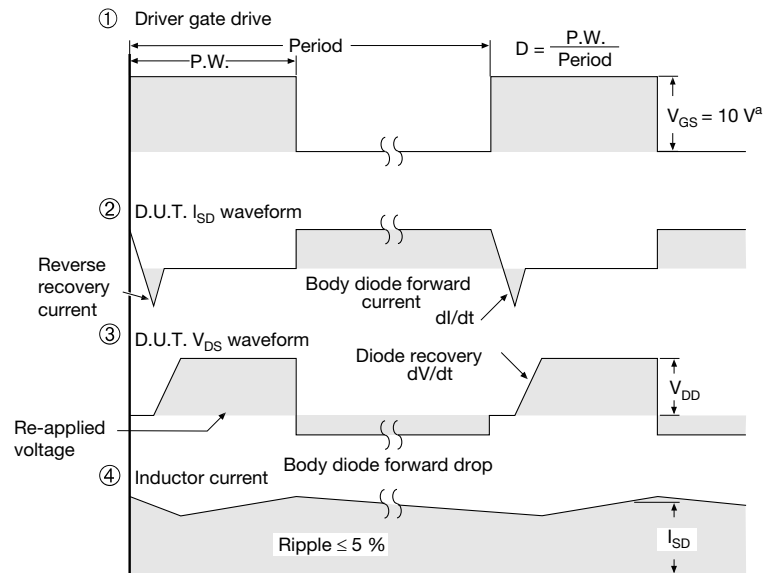
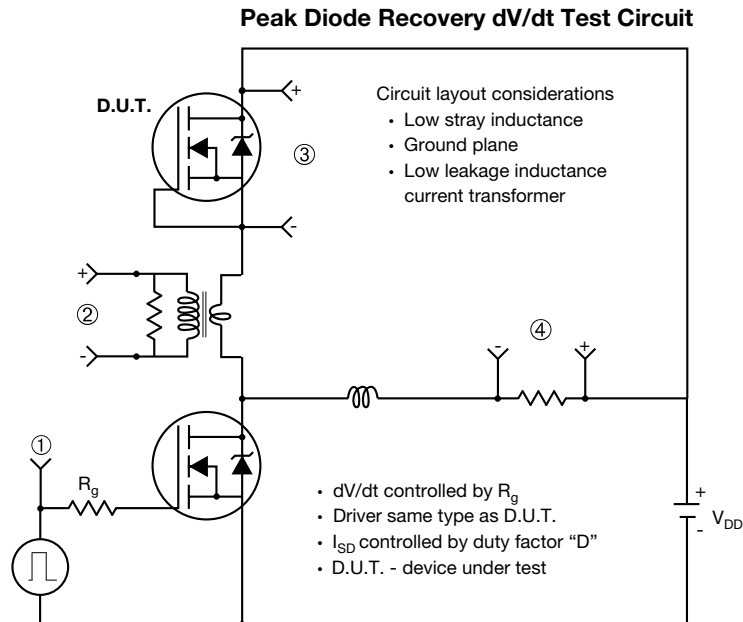


Fig. 13b - Gate Charge Test Circuit

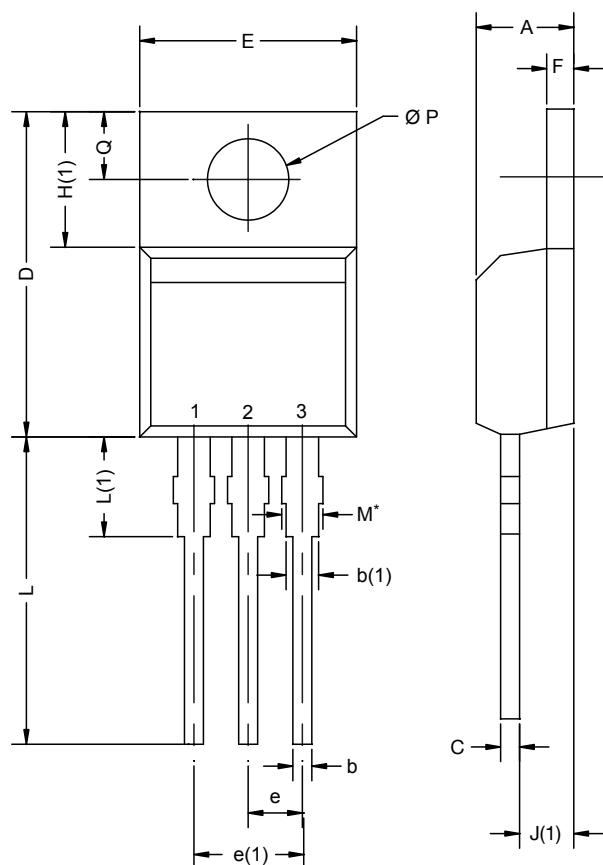


**Note**

a.  $V_{GS} = 5V$  for logic level devices

**Fig. 14 - For N-Channel**

## TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
ECN: X12-0208-Rev. N, 08-Oct-12 DWG: 5471				

### Notes

\* M = 1.32 mm to 1.62 mm (dimension including protrusion)  
Heatsink hole for HVM



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